TOSHIBA BIPOLAR LINEAR INTEGRATED CIRCUIT SILICON MONOLITHIC

TA8210AH, TA8210AL

20W BTL × 2CH AUDIO POWER AMPLIFIER

The thermal resistance θ j-T of TA8210AH, TA8210AL package designed for low thermal resistance, has a high efficiency of heat radiation.

The temperature rise of chip can be reduced, and the influence from the degradation of the features due to the temperature rise at the high output can also be reduced.

This stereo audio power IC, designed for car audio use, has two built-in channels to reduce the characteristic difference between L and R channels.

In addition, the functions of stand-by and muting, and a variety of protection circuits are involved.

FEATURES

- Low Thermal Resistance : θj -T = 1.5°C/W (Infinite Heat Sink)
- High Power
 - : POUT (1) = 22W (Typ.) / Channel $(V_{CC} = 14.4V, f = 1kHz, THD = 10\%, R_L = 4\Omega)$ POUT (2) = 19W (Typ.) / Channel $(V_{CC} = 13.2V, f = 1kHz, THD = 10\%, R_L = 4\Omega)$
- Low Distortion Ratio : THD = 0.04% (Typ.) (V_{CC} = 13.2V, f = 1kHz, P_{OUT} = 1W, R_L = 4 Ω , G_V = 50dB)
- Low Noise : $V_{NO} = 0.30 \text{mV}_{rms}$ (Typ.) ($V_{CC} = 13.2\text{V}$, $R_L = 4\Omega$, $G_V = 50 \text{dB}$, $R_g = 0\Omega$, $BW = 20 \text{Hz} \sim 20 \text{kHz}$)
- Built-in Stand-by Function (With pin 4) set a LOW, power is turned OFF.) : $I_{SB} = 1 \mu A$ (Typ.)
- Built-in Muting Function (With pin① set at LOW, power is turned OFF.) : V (Mute) = 1V (Typ.)
- Built-in Various Protection Circuits Protection circuits : Thermal Shut Down, over voltage, out→V_{CC} short, out→GND short and OUT-OUT Short.
- Operating Supply Voltage : V_{CC} = 9~18V 980508EBA: TOSHIBA is continually working to improve the quality and the reliability of its products. Nevertheless, semiconductor devices in general can malfunction or fail due to their inherent electrical sensitivity and vulnerability to physical stress. It is the responsibility of the buyer, when utilizing TOSHIBA products, to observe standards of safety, and to avoid situations in which a malfunction or failure of a TOSHIBA product could cause loss of human life, bodily injury or damage to property. In developing your designs, please ensure that TOSHIBA products are used within specified operating ranges as set forth in the most recent products specifications. Also, please keep in mind the precautions and conditions set forth in the TOSHIBA Semiconductor Reliability Handbook. The products described in this document are subject to foreign exchange and foreign trade laws. The information contained herein is presented only as a guide for the applications of our products. No responsibility is assumed by TOSHIBA CORPORATION for any infringements of intellectual property or other rights of TOSHIBA CORPORATION or others. I the information contained herein is subject to change without notice.



980508FBA2

BLOCK DIAGRAM

TA8210AH, TA8210AL ($G_V = 50dB$)



CAUTIONS AND APPLICATION METHOD

(Description is made only on the single channel.)

1. Voltage gain adjustment



This IC has the amplifier construction as shown in Fig.1. The Pre-Amp (Amp 1) is provided to the primary stage, and the input voltage is amplified by the Flat Amps, Amp 3 and Amp 4 of each channel through the phase Amp (Amp 2).

Since the input offset is prevented by Pre-Amp when V_{CC} is set to ON, this circuit can remarkably reduce the pop noise.

The total closed loop gain G_V of this IC can be obtained by expression below when the closed loop voltage gain of Amp 1 is G_{V1} .

$$G_{V1} = 20 \ell og \quad \frac{R1 + (R_f + R2)}{R_f + R2} \quad (dB) \quad \dots \qquad (1)$$

The closed loop voltage gain of POWER Amp, Amp 3 and Amp 4 is fixed at $G_{V3} = G_{V4} = 20$ dB.

Therefore, the total closed circuit voltage gain G_V is obtained through BTL connection by the expression below.

 $G_V = G_{V1} + G_{V3} + 6$ (dB) (2)

For example, when $R_f = 0\Omega$, G_V is obtained by the expressions (1) and (2) as shown below.

$$G_V \rightleftharpoons 24 + 20 + 6 = 50 dB$$

The voltage gain is reduced when R_f is increased. (Fig.2) With the voltage gain reduced, since (1) the oscillation stability is reduced, and (2) the pop noise changes when V_{CC} is set to ON, refer to the items 3 and 4.



Fig.2

2. Stand-by SW function

By means of controlling pin (Stand-by terminal) to High and Low, the power supply can be set to ON and OFF. The threshold voltage of pin (is set at 2.1V ($3V_{BE}$), and the Power Supply current is about $1\mu A$ (Typ.) at the stand-by state.

STAND-BY	POWER	V _(SB) (V)			
ON	OFF	0~2			
OFF	ON	3~Vcc			

Pin (control voltage : V (SB)

Advantage of stand-by SW

- (1) Since V_{CC} can directly be controlled to ON/OFF by the microcomputer, the switching relay can be omitted.
- (2) Since the control current is microscopic, the switching relay of small current capacity is satisfactory for switching.



Fig.3 With pin 4 set to High, Power is turned ON.



(Standby Switch Method)

3. Preventive measure against oscillation

For preventing the oscillation, it is advisable to use C_4 , the condenser of polyester film having small characteristic fluctuation of the temperature and the frequency.

The resistance R to be series applied to C_4 is effective for phase correction of high frequency, and improves the oscillation allowance.

Since the oscillation allowance is varied according to the causes described below, perform the temperature test to check the oscillation allowance.

- (1) Voltage gain to be used (G_V Setting)
- (2) Capacity value of condenser
- (3) Kind of condenser
- (4) Layout of printed board

In case of its use with the voltage gain G_V reduced or with the feedback amount increased, care must be taken because the phase-inversion is caused by the high frequency resulting in making the oscillation viably generated.

4. Input offset prevention circuit at $V_{CC} \rightarrow ON$

Having the Pre-Amp (Amp 1) mounted on the primary stage, this IC contains the circuit for making the Amp 1 input voltage and the NF terminal voltage equipotential.

Therefore, the offset voltage produced at the input stage is suppressed to prevent the pop noise at $V_{CC} \rightarrow ON$. The capacity values of the input and NF condenser (C₁ and C₂) shall be set according to the gain to be used.

(Reference) (A)At $G_V = 50dB$ ($R_f = 0\Omega$) $C_1 = 4.7\mu F$, $C_2 = 47\mu F$ (B) At $G_V = 40dB$ ($R_f = 470\Omega$) $C_1 = 3.3\mu F$, $C_2 = 33\mu F$

<u>TOSHIBA</u>

5. Muting function

Through setting pin 1 (mute terminal) at about 1V or less, muting becomes possible. The interval circuit of IC is shown in Fig.4.

When pin is set to LOW, Q1 and Q2 are turned to ON, the charge of the ripple condenser is discharged and the bias is cut. The mute amount of 60dB or over can be obtained.

Since this muting function rapidly discharge the charge of the ripple filter capacitor of pin[®], the pop noise is generated by the DC fluctuation of the bias section.

Therefore, this muting function is not appropriate to the audio muting but it is effective in muting at $V_{CC} \rightarrow ON$.



Fig.4 Mute circuit

6.	External	part	list	and	description
•••	External	P			accentration

сум	SYM- RECOM-		INFLU	REMARKS		
BOL VALUE FEATURE		FEATURE	SMALLER THAN LARGER THAN RECOMMENDED VALUE RECOMMENDED VALUE			
C ₁	4.7 μF	DC blocking	Related to pop noise at	Related to gain.		
					Refer to item 4.	
			Related to pop noise at			
$1 C_{2} = 47 \mu F_{1}$	Feedback	Determination of low cu				
	condenser	1				
		$C_2 = \frac{1}{2\pi \cdot f_L \cdot R_f}$				
C ₃	220 μF	Ripple	Time constant is small	Time constant is large		
<u>_3</u>	220µ1	reduction	at V _{CC} →ON or OFF.	at V _{CC} →ON or OFF.		
	C ₄ 0.12μF	Oscillation	Made liable to	Oscillation allowance.	Refer to item 3.	
∽4		prevention	oscillate.	Oscillation anowance.	Refer to Refit 5.	
			For filtering power supply hum and ripple.			
C ₅ 1000 μ F Ripple filter		Ripple filter	Large at using AC rectif			
			Small at using DC powe			
Ca	C ₆ 1000pF Oscillation		Oscillation allowance im	Refer to item 3.		
C ₆ 1000pF		prevention	Noise Reduction			

MAXIMUM RATINGS (Ta = 25° C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Peak Supply Voltage (0.2s)	V _{CC} (surge)	50	V
DC Supply Voltage	VCC (DC)	25	V
Operating Supply Voltage	V _{CC} (opr)	18	V
Output Current (Peak)	lO (peak)	9	Α
Power Dissipation	PD	50	W
Operating Temperature	T _{opr}	- 30~85	°C
Storage Temperature	T _{stg}	- 55~150	°C
FLECTRICAL CHARACTERISTICS	•		

ELECTRICAL CHARACTERISTICS (Unless otherwise specified, $V_{CC} = 13.2V$, $R_L = 4\Omega$, f = 1kHz, $Ta = 25^{\circ}C$)

CHARACTERISTIC	SYMBOL	TEST CIR- CUIT	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Quiescent Supply Current	lccQ	—	V _{IN} = 0		120	250	mA
Output Power	POUT (1)	—	V _{CC} = 14.4V, THD = 10%		22	—	w
	POUT (2)	—	THD = 10%	16	19	—	VV I
Total Harmonic Distortion Ratio	THD	-	P _{OUT} = 1W	_	0.04	0.4	%
Voltage Gain	GV	-	—	48	50	52	dB
Output Noise Voltage	V _{NO}	-	$R_g = 0\Omega$, BW = 20Hz~20kHz	_	0.30	0.70	mV _{rms}
Ripple Rejection Ratio	R.R.	-	fripple = 100Hz, R _g = 600 Ω	40	54	_	dB
Input Resistance	R _{IN}	-	—	_	30	—	kΩ
Output Offset Voltage	Voffset	—	V _{IN} = 0	- 0.3	0	0.3	mV
Current at Stand-by State	ISB	—	—	_	1	10	μΑ
Cross Talk	C.T.	-	R _g = 600Ω, V _{OUT} = 0.775V _{rms} (0dBm)	_	60	_	dB
Pin④ Control Voltage	V _{SB}	_	Stand-by→OFF (Power→ON)	2.5	_	V _{CC}	v
Pin ${f 1}$ Control Voltage	V (Mute)	_	Mute→ON (Power→OFF)	_	1.0	2.0	v

TEST CIRCUIT

TA8210AH, TA8210AL ($G_V = 50dB$)



<u>TOSHIBA</u>





OUTLINE DRAWING HZIP17-P-2.00

Unit : mm



Weight : 9.8g (Typ.)

OUTLINE DRAWING HSIP17-P-2.00



17

Weight : 9.8g (Typ.)

1